| A | Re | g. No. : | | | | | | | | | | | |
|------|---|-------------|--------|-------|-------|-------|--------|-------|-------|------|--|-----------|-------------|
| | Qu | estion P | ape | r Co | ode | : R2 | 2300 | 6 | | | | | |
| | B E /B Tech. DEGREE EXAMINATION MAY 2024 | | | | | | | | | | | | |
| | Second Semester | | | | | | | | | | | | |
| | Electrical and Electronics Engineering | | | | | | | | | | | | |
| | R21UEE206 PRINCIPLES OF ELECTRONICS | | | | | | | | | | | | |
| | | (Reg | ulatio | ons F | R202 | 1) | | | | | | | |
| Dura | Duration: Three hours Maximum: 100 Mark | | | | | | | | | 5 | | | |
| | | Answ | er A | ll Qu | estic | ons | | | | | | | |
| | PART A - $(10 \text{ x } 1 = 10 \text{ Marks})$ | | | | | | | | | | | | |
| 1. | What type of semiconductor has excess holes as charge carriers? | | | | | | | CO | 1- U | | | | |
| | (a) P-type semiconductor | | | (ł | o) N- | type | sem | icon | duct | or | | | |
| | (c) Intrinsic semiconductor | | | (0 | l) Ex | trins | sic se | emico | ondu | ctor | | | |
| 2. | Which process involves charge carriers moving from high to low CO1- U concentration? | | | | | | | | 1- U | | | | |
| | (a) Drift | | | | (b) E | Diffu | sion | | | | | | |
| | (c) Band bending | | | | (d) R | lecoi | mbin | ation | 1 | | | | |
| 3. | In a common-emitter comprimarily illustrate? | nfiguration | , wł | nat c | lo in | nput | cha | racte | risti | cs | | CO | 1- U |
| | (a) Relationship between base current and collector-emitter voltage. | | | | | | | | | | | | |
| | (b) Relationship between base current and base-emitter voltage. | | | | | | | | | | | | |
| | (c) Relationship between collector current and collector-emitter voltage | | | | | | | | | | | | |
| | (d) Relationship between emitter current and emitter-base voltage. | | | | | | | | | | | | |
| 4. | What is the significance of the hybrid- π model in transistor analysis? CO1 - | | | | | | | 1- U | | | | | |
| | (a) A) Simplifies analysis by representing transistor with resistors and capacitors. | | | | | | | | | | | | |
| | (b) Provides detailed breakdown of transistor behavior. | | | | | | | | | | | | |
| | (c) Measures transistor performance in RF applications. | | | | | | | | | | | | |
| | (d) Determines transistor's thermal characteristics | | | | | | | | | | | | |

| 5. | What defines the operation of a JFET? | | | | | | | |
|-----|---------------------------------------|--|--|-------------------------------------|-------------------|--|--|--|
| | (a) Voltage-controlled resistance. | | | (b) Current-controlled res | sistance. | | | |
| | (c) Vo | pacitance. | | | | | | |
| 6. | Which | CO1- U | | | | | | |
| | (a) Junction isolation | | | (b) Dielectric isolation | | | | |
| | (a) Barrier | | | (b) Monoelectric isolation | 1 | | | |
| 7. | BJT sr | BJT small-signal analysis commonly employs which model? | | | | | | |
| | (a) Hy | brid-π | | (b) Ebers-Moll | | | | |
| | (c) T | | | (d) H | | | | |
| 8. | Where | CO1- U | | | | | | |
| | (a) Base (b) Collector | | | (c) Emitter | (d) Substrate | | | |
| 9. | What i | CO1-U | | | | | | |
| | (a) Ma | ximum voltage | gain | (b) Maximum current gai | n | | | |
| | (c) Un | (c) Unity loop gain with 360° phase shift (d) Unity loop gain with 180° | | | | | | |
| 10. | Which for free | ilizes inductors and capacitors | s CO1-U | | | | | |
| | (a) LC | -Hartley | | (b) RC-Phase shift | | | | |
| | (c) Crystal oscillator | | | (d) Wein Bridge | | | | |
| | | | PART – B (5 : | x 2= 10 Marks) | | | | |
| 11. | Descri | CO1- U | | | | | | |
| 12. | Descri a bipol | ns in CO2-App | | | | | | |
| 13. | Identif | CO1-U | | | | | | |
| 14. | Explai | CO1- U | | | | | | |
| 15. | Why q | CO4-App | | | | | | |
| | | | PART – C (| 5 x 16= 80 Marks) | | | | |
| 16. | (a) E | Explain the commenced of the commenced o | oncept of drift a and their roles in curr | and diffusion carriers in ent flow. | CO1-U (16) | | | |

Or

- (b) Draw the V-I characteristics of P-N junctions diode with their **CO1-U** (16) input and output characteristics
- 17. (a) Analyze the formation of PNP and NPN junctions in a Bipolar CO3 Ana (16) Junction Transistor (BJT). How does the doping of semiconductor materials contribute to the creation of these junctions?

Or

- (b) Analyze the relationship between α , β , and γ in a BJT. Discuss **CO3 Ana** (16) how changes in these parameters affect the transistor's behavior in different configurations.
- 18. (a) Analyze the impact of channel width modulation on the output CO5 Ana (16) characteristics of a FET and how it affects the device performance.

Or

- (b) Analyze the key characteristics of JFETs, including trans CO5 Ana (16) conductance, pinch-off voltage, and input impedance, and their significance in device applications.
- 19. (a) Draw the circuit diagram of a voltage series feedback amplifier CO 4- App (16) and derive expressions for voltage gain with and without feedback.

Or

- (b) Draw the circuit diagram of a current series feedback amplifier CO 4- App (16) and derive expressions for voltage gain with and without feedback.
- 20. (a) With a neat sketch, explain the working of an astable CO1 U (16) multivibrator.

Or

(b) With a neat sketch, explain the working of an Monostable **CO1 - U** (16) multivibrator.

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